

# QSC112, QSC113, QSC114 Plastic Silicon Infrared Phototransistor

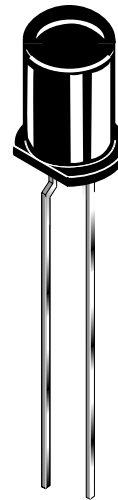
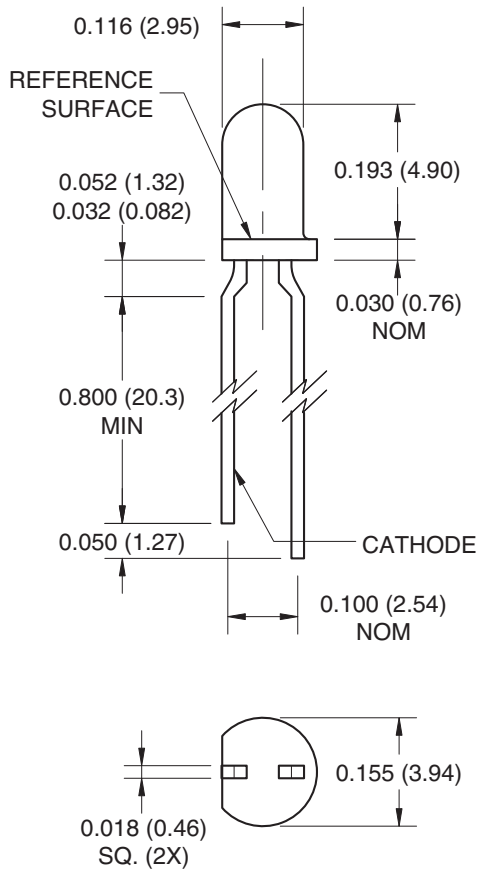
## Features

- Tight production distribution
- Steel lead frames for improved reliability in solder mounting
- Good optical-to-mechanical alignment
- Plastic package is infrared transparent black to attenuate visible light
- Can be used with QECXXX LED
- Black plastic body allows easy recognition from LED

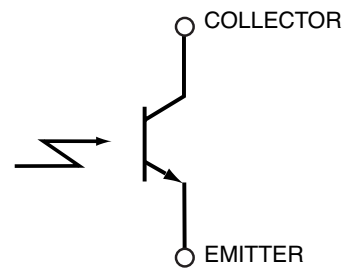
## Description

The QSC112/113/114 is a silicon phototransistor encapsulated in an infrared transparent, black T-1 package.

## Package Dimensions



## Schematic



### Notes:

1. Dimensions of all drawings are in inches (mm).
2. Tolerance is  $\pm 0.10$  (.25) on all non-nominal dimensions unless otherwise specified.

**Absolute Maximum Ratings** ( $T_A = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Rating	Units
Operating Temperature	$T_{OPR}$	-40 to +100	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-40 to +100	$^\circ\text{C}$
Soldering Temperature (Iron) <sup>(2,3,4)</sup>	$T_{SOL-I}$	240 for 5 sec	$^\circ\text{C}$
Soldering Temperature (Flow) <sup>(2,3)</sup>	$T_{SOL-F}$	260 for 10 sec	$^\circ\text{C}$
Collector-Emitter Voltage	$V_{CE}$	30	V
Emitter-Collector Voltage	$V_{EC}$	5	V
Power Dissipation <sup>(1)</sup>	$P_D$	100	mW

1. Derate power dissipation linearly 1.33 mW/ $^\circ\text{C}$  above 25 $^\circ\text{C}$ .
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron 1/16" (1.6mm) minimum from housing.
5.  $\lambda = 880$  nm, AlGaAs.

**Electrical / Optical Characteristics** ( $T_A = 25^\circ\text{C}$ )

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
Peak Sensitivity Wavelength		$\lambda_{PS}$	–	880	–	nm
Reception Angle		$\theta$	–	$\pm 8$	–	Deg.
Collector-Emitter Dark Current	$V_{CE} = 10$ V, $E_e = 0$	$I_{CEO}$	–	–	100	nA
Collector-Emitter Breakdown	$I_C = 1$ mA	$BV_{CEO}$	30	–	–	V
Emitter-Collector Breakdown	$I_E = 100$ $\mu\text{A}$	$BV_{ECO}$	5	–	–	V
On-State Collector Current QSC112	$E_e = 0.5$ mW/cm <sup>2</sup> , $V_{CE} = 5$ V <sup>(5)</sup>	$I_{C(ON)}$	1	–	4	mA
On-State Collector Current QSC113			2.40	–	9.60	
On-State Collector Current QSC114			4.00	–	–	
Saturation Voltage	$E_e = 0.5$ mW/cm <sup>2</sup> , $I_C = 0.5$ mA <sup>(5)</sup>	$V_{CE(sat)}$	–	–	0.4	V
Rise Time	$V_{CC} = 5$ V, $R_L = 100$ $\Omega$ , $I_C = 2$ mA	$t_r$	–	5.0	–	$\mu\text{s}$
Fall Time		$t_f$	–	5.0	–	

## Typical Performance Curves

Figure 1. Light Current vs. Radiant Intensity

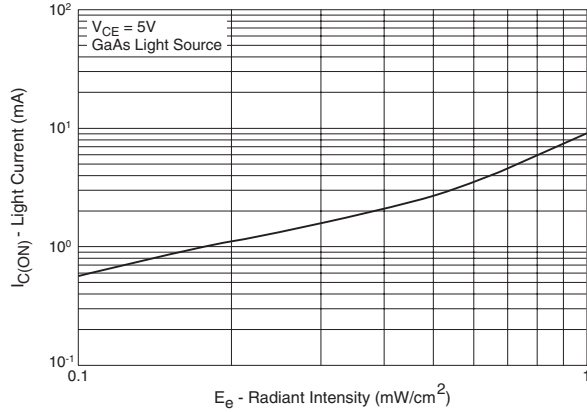


Figure 2. Angular Response Curve

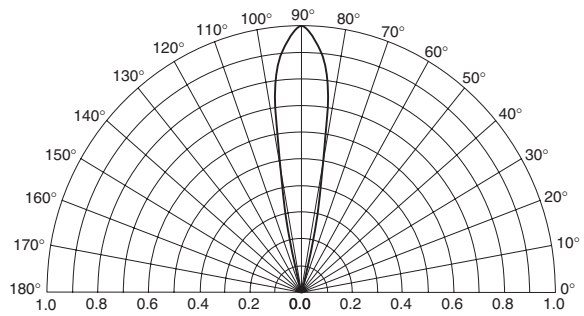


Figure 3. Dark Current vs. Collector - Emitter Voltage

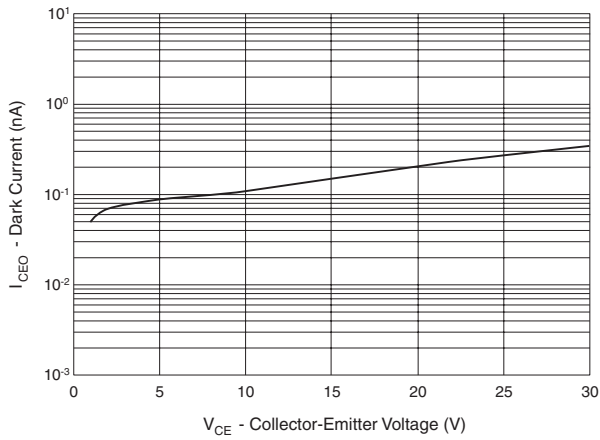


Figure 4. Light Current vs. Collector - Emitter Voltage

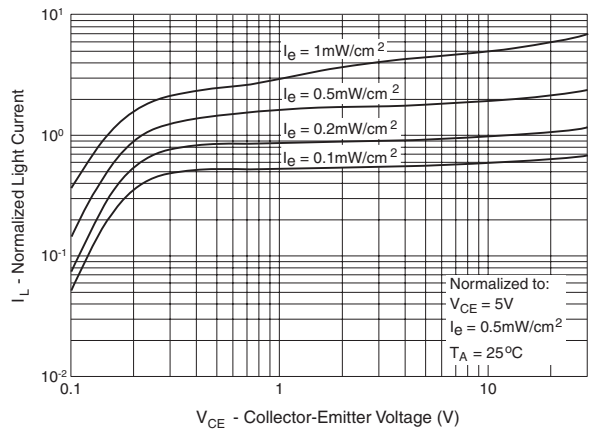
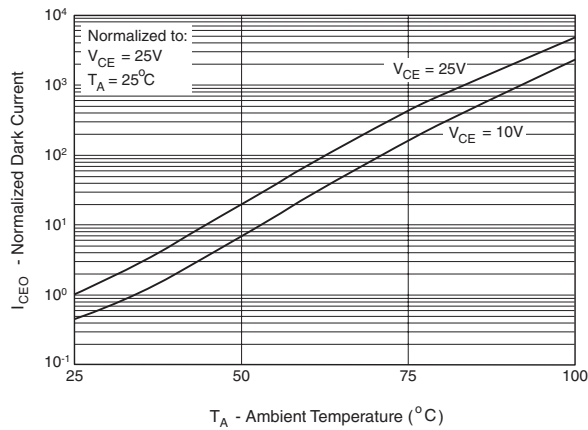


Figure 5. Dark Current vs. Ambient Temperature



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Rev. 116